



JST16F-800C 16A TRIAC

Rev.A.1.1

- o : C m B s



Peak gate power	P_{GM}	10	W
Peak pulse voltage ($T_j=25$; non-repetitive, off-state; FIG.7)	V_{pp}	3.5	kV

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ORDERING INFORMATION

J	ST	16	F	-800	C
JieJie Microelectronics Co., Ltd.	Triacs	$I_{T(RMS)}:16A$			$C:I_{GT1-3} 0.25mA \ I_{GT4} 0.50mA$
		F:TO-220F(Ins)		800: $V_{DRM} / V_{RRM} 1800V$	

MARKING

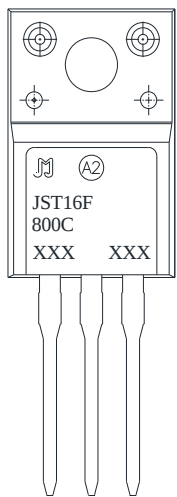


FIG.1: Maximum power dissipation versus RMS on-state current

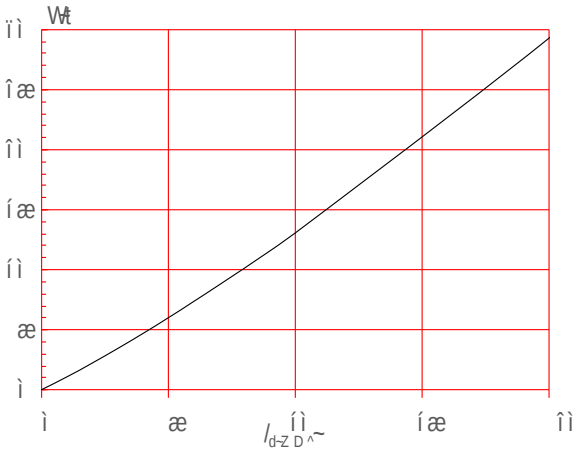
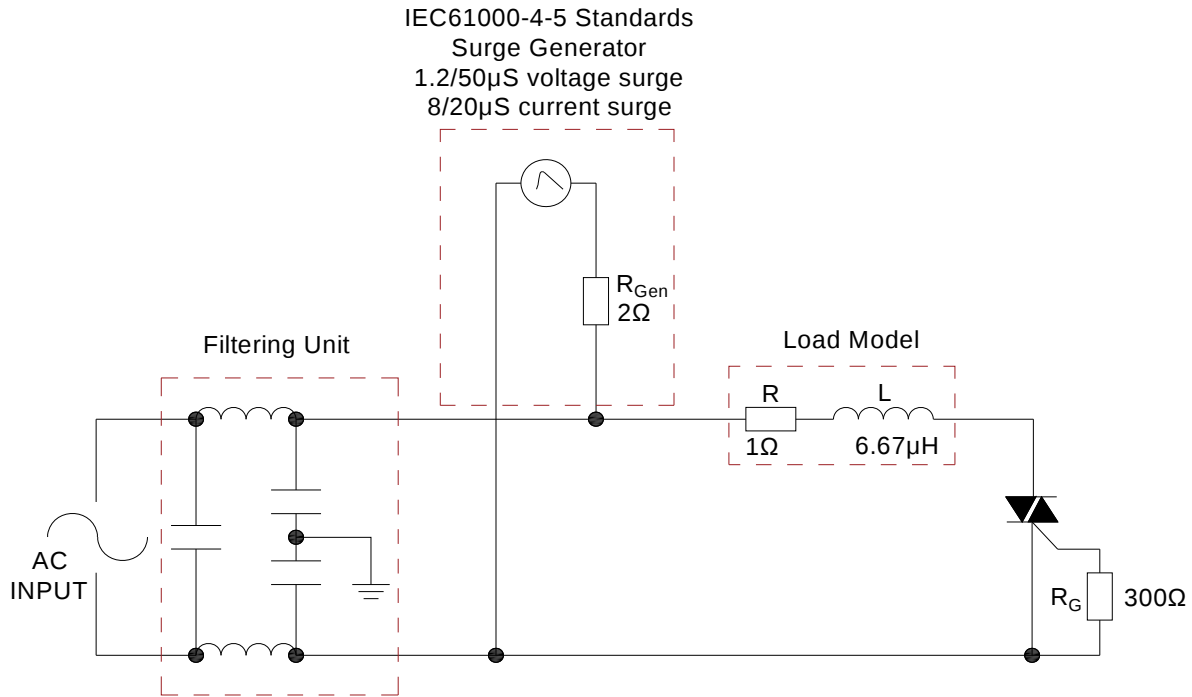


FIG.2: RMS on-state current versus case temperature



FIG.7 ÖTest circuit for inductive and resistive loads to IEC-61000-4-5 standards



LEAD FORMING AND SOLDERING



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